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Vishay/Siliconix SUD50P06-15-GE3

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SUD50P06-15

Vishay Siliconix

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$				
- 60	0.015 at V _{GS} = - 10 V	- 50 ^d			
- 60	0.020 at V _{GS} = - 4.5 V	- 50 ^d			

TO-252 Drain Connected to Tab Top View

Ordering Information

SUD50P06-15-GE3 (Lead (Pb)-free and Halogen-free) SUD50P06-15-T4-GE3 (Lead (Pb)-free and Halogen-free)

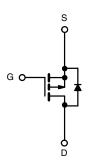
FEATURES

- TrenchFET® Power MOSFET
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 60	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	I _D	- 50 ^d	А		
Continuous Diam Guirent (1) = 173 C)	T _C = 125 °C	טי [- 27.5			
Pulsed Drain Current	I _{DM}	- 80				
Avalanche Current	I _{AS}	- 50				
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ		
Paular Discinction	T _C = 25 °C	В	113 ^c	W		
Power Dissipation	T _A = 25 °C	P _D	2.5 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
li un akin un kan Auralai aurakh	t ≤ 10 s	- R _{thJA}	15	18		
Junction-to-Ambient ^b	Steady State		40	50	°C/W	
Junction-to-Case		R _{thJC}	0.82	1.1		

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.

Document Number: 68940 S12-2439 Rev. C, 15-Oct-12

For technical questions, contact: pmostechsupport@vishav.comm

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Datasheet of SUD50P06-15-GE3 - MOSFET P-CH 60V 50A TO-252

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SUD50P06-15

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	1			1	1		
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, } I_D = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	•	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			- 50	μА	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 100		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			Α	
		V _{GS} = - 10 V, I _D = - 17 A		0.012	0.015		
Dutings on On Ohata Basistanas	D	V _{GS} = - 10 V, I _D = - 50 A, T _J = 125 °C			0.025		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 50 A, T _J = 150 °C			0.028 Ω		
		V _{GS} = - 4.5 V, I _D = - 14 A			0.020		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S	
Dynamic ^b							
Input Capacitance	C _{iss}			4950			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		480		pF	
Reverse Transfer Capacitance	C _{rss}]		405			
Total Gate Charge ^c	Q_g			110	165		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -50 \text{ A}$		19		nC	
Gate-Drain Charge ^c	Q_{gd}]		28			
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 0.6 Ω		70	105	ns ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 50 A, V_{GEN} = - 10 V, R_G = 6 Ω		175	260		
Fall Time ^c	t _f]		175	260		
Source-Drain Diode Ratings and Cha	aracteristics	T _C = 25 °C ^b		•	,		
Continuous Current	Is				- 50	^	
Pulsed Current	I _{SM}				- 80	Α	
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1	- 1.6	V	
Reverse Recovery Time	t _{rr}	I _F = - 50 A, dI/dt = 100 A/μs		45	70	ns	

Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

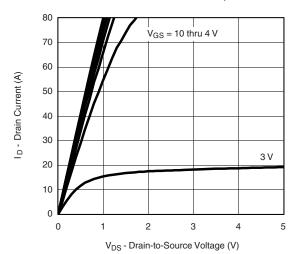




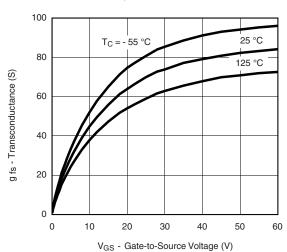
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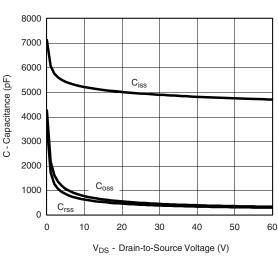
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



Transconductance

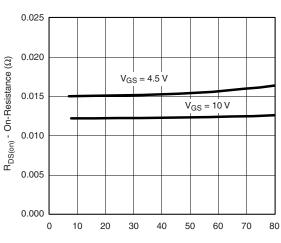


Capacitance

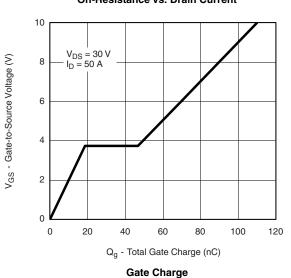
70 60 ID - Drain Current (A) 50 40 30 T_C = 125 °C 20 25 10 55 °C 0.0 0.5 1.0 2.0 2.5 3.0 3.5 4.0

Transfer Characteristics

V_{GS} - Gate-to-Source Voltage (V)



ID - Drain Current (A) On-Resistance vs. Drain Current



Document Number: 68940 S12-2439 Rev. C, 15-Oct-12 For technical questions, contact: pmostechsupport@vishav.comm

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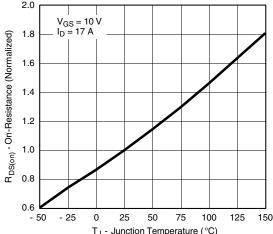
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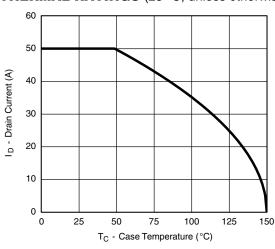


On-Resistance vs. Junction Temperature

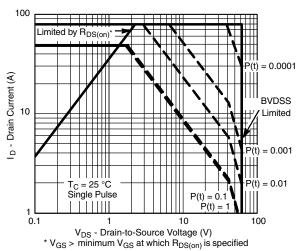
Is - Source Current (A) T_{.1} = 150 °C T_J = 25 °C 10 0.0 0.3 0.6 1.2 1.5 V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

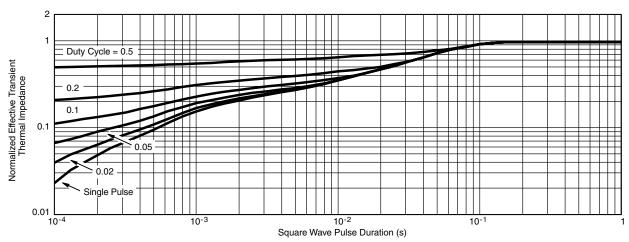
THERMAL RATINGS (25 °C, unless otherwise noted)



Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68940.

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Datasheet of SUD50P06-15-GE3 - MOSFET P-CH 60V 50A TO-252

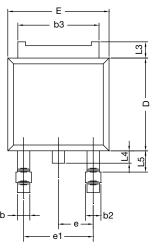
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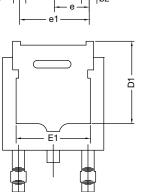


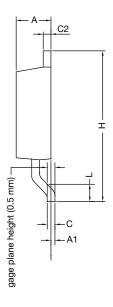
Package Information

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TO-252AA Case Outline







	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	ı	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347					

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• Dimension L3 is for reference only.

Revision: 16-May-16 Document Number: 71197



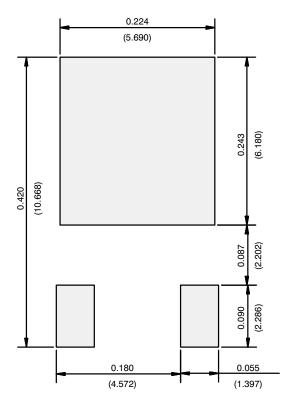




Application Note 826

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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